# **Panasonic**

MOS FET

### FCAB21490L1

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### Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

#### ■ Features

- Source-source ON resistance:RSS(on) typ. = 2.2 m $\Omega$ (VGS = 3.8 V)
- CSP(Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)
- Marking Symbol: 7F

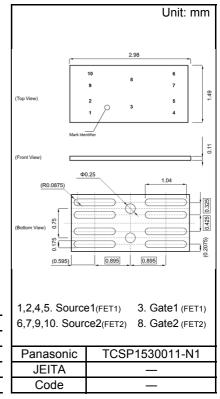
#### ■ Packaging

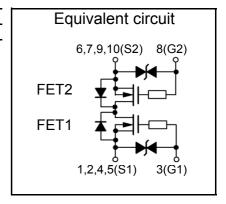
Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

| Parameter                 |          | Symbol | Rating      | Unit |  |
|---------------------------|----------|--------|-------------|------|--|
| Source-source Voltage     |          | VSS    | 12          | V    |  |
| Gate-source Voltage       |          | VGS    | ±8          | V    |  |
| Source Current            | DC *1    | IS1    | 13.5        | Α    |  |
|                           | DC *2    | IS2    | 29          | Α    |  |
|                           | Pulse *3 | ISp    | 135         | Α    |  |
| Total Power Dissipation   | DC *1    | PD1    | 0.54        | W    |  |
|                           | DC *2    | PD2    | 3.5         | W    |  |
| Channel Temperature       |          | Tch    | 150         | °C   |  |
| Storage Temperature Range |          | Tsta   | -55 to +150 | °C   |  |

- Note \*1 Mounted on FR4 board ( 25.4 mm  $\times$  25.4 mm  $\times$  t1.0 mm ) using the minimum recommended pad size (36 $\mu$ m Copper ).
  - \*2 Mounted on Ceramic substrate (70 mm × 70 mm × t1.0 mm).
  - \*3  $t = 10 \mu s$ , Duty Cycle  $\leq 1 \%$





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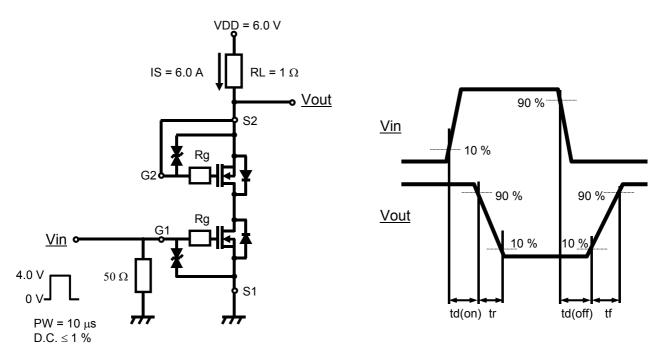
### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

| Parameter                         | Symbol   | Conditions                                 | Min  | Тур  | Max  | Unit |  |
|-----------------------------------|----------|--|------|------|------|------|--|
| Source-source Breakdown Voltage   | VSSS     | IS = 1.0 mA, VGS = 0 V                     | 12   |      |      | V    |  |
| Zero Gate Voltage Source Current  | ISSS     | VSS = 12 V, VGS = 0 V                      |      |      | 1.0  | μА   |  |
| Gate-source Leakage Current       | IGSS     | $VGS = \pm 8 \text{ V}, VSS = 0 \text{ V}$ |      |      | ±10  | ^    |  |
|                                   |          | VGS = ±5 V, VSS = 0 V                      |      |      | ±1.0 | μΑ   |  |
| Gate-source Threshold Voltage     | Vth      | IS = 1.11 mA, VSS = 10 V                   | 0.35 | 0.90 | 1.4  | V    |  |
| Source-source On-state Resistance | RSS(on)1 | IS = 6.0 A, VGS = 4.5 V                    | 1.55 | 2.1  | 2.75 |      |  |
|                                   | RSS(on)2 | IS = 6.0 A, VGS = 3.8 V                    | 1.6  | 2.2  | 2.85 | mΩ   |  |
|                                   | RSS(on)3 | IS = 6.0 A, VGS = 3.1 V                    | 1.65 | 2.4  | 3.95 |      |  |
|                                   | RSS(on)4 | IS = 6.0 A, VGS = 2.5 V                    | 1.9  | 3.1  | 6.1  |      |  |
| Body Diode Forward Voltage        | VF(s-s)  | IF = 6.0 A, VGS = 0 V                      |      | 0.6  | 1.2  | V    |  |
| Input Capacitance *1              | Ciss     |  |      | 3570 |      | pF   |  |
| Output Capacitance *1             | Coss     | VSS = 10 V, VGS = 0 V, f = 1 kHz           |      | 460  |      |      |  |
| Reverse Transfer Capacitance *1   | Crss     |  |      | 410  |      |      |  |
| Turn-on delay Time *1,*2          | td(on)   | VDD = 6.0 V, VGS = 0 to 4.0 V              |      | 0.7  |      | μS   |  |
| Rise Time *1,*2                   | tr       | IS = 6.0 A                                 |      | 1.5  |      |      |  |
| Turn-off delay Time *1,*2         | td(off)  | VDD = 6.0 V, VGS = 4.0 to 0 V              |      | 6.7  |      | μS   |  |
| Fall Time *1,*2                   | tf       | IS = 6.0 A                                 |      | 4.1  |      |      |  |
| Total Gate Charge *1              | Qg       | VDD = 6.0 V                                |      | 25   |      |      |  |
| Gate-source Charge *1             | Qgs      | VGS = 0 to 4.0 V,                          |      | 12   |      | nC   |  |
| Gate-drain Charge *1              | Qgd      | IS = 6.0 A                                 |      | 6    |      |      |  |

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

- \*1 Guaranteed by design, not subject to production testing
- \*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

#### Note2:Measurement circuit

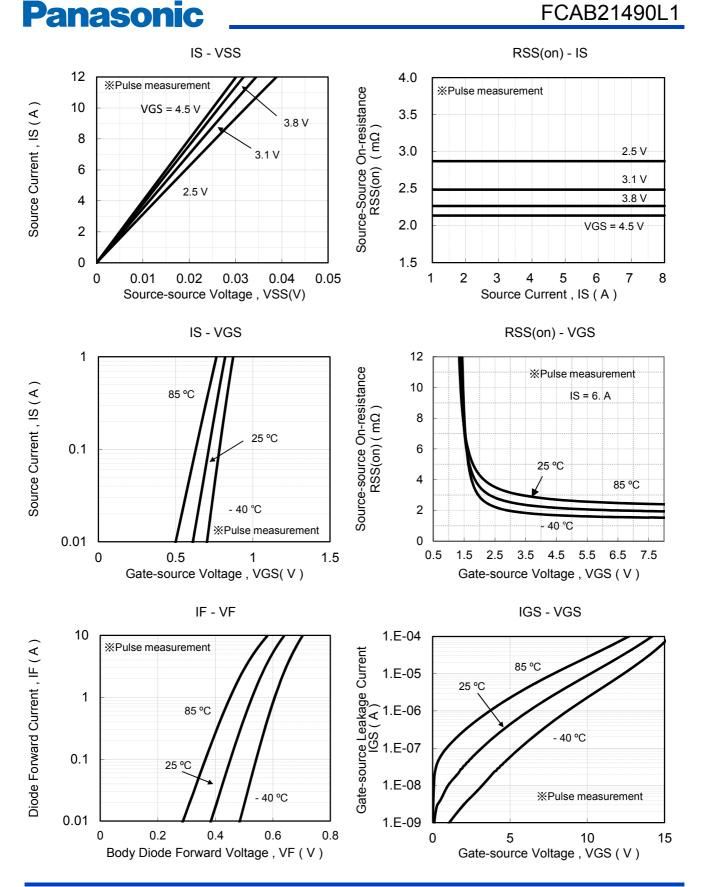


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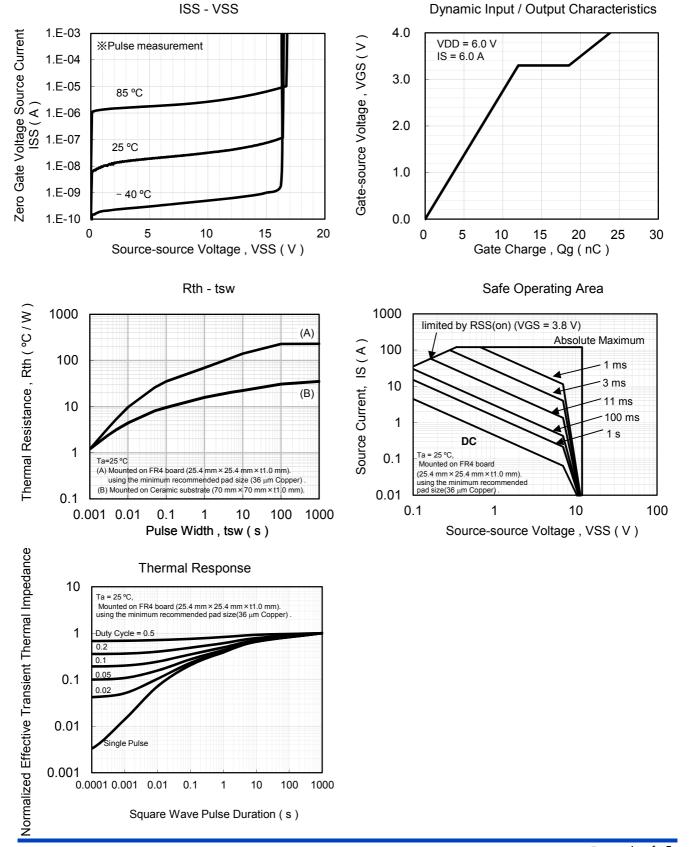
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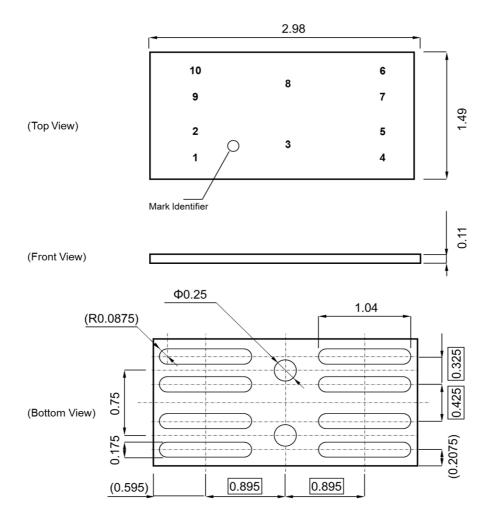
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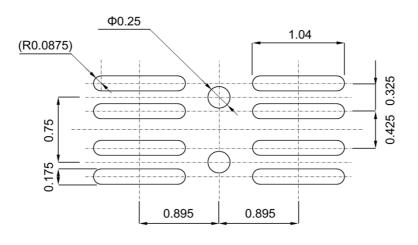
■ Outline

Unit: mm



## ■ Land Pattern (Reference)

Unit: mm



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